



PATENT  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Han-Sin Lee, et al. -  
Serial No.: 09/775,231 -  
Filing Date: February 1, 2001 -  
Title: Trench Isolation Method

Examiner: Pompey, Ron E. *Arndt*  
Group Art Unit: 2812

#15/c

*J. Mainella*

7/16/03

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AMENDMENT C

Sir:

The following is in response to the Office Action dated March 26, 2003, and is filed within the shortened statutory period of three months.

In the specification:

Please amend the paragraph at page 5 line 12 through page ~~5~~<sup>5</sup> line ~~17~~<sup>22</sup> as follows:

C1 (Amended) In order to prevent the inner wall of the trench 17 from additionally being oxidized, a silicon nitride layer, i.e., oxidation barrier layer 20 is formed on an overall surface of the resulting structure where the oxide layer 19 is formed. It is preferable that a capping layer 21, for example, CVD oxide layer for protecting the oxidation barrier layer 20, is formed on the oxidation barrier layer 20. The capping layer 21 prevents damage of the oxidation barrier layer 20 in the following process for forming an insulating layer which fills a trench.